

10/773,228, Inter Ference, Class and Text SEARCH, REA
12-1-05.

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	233	((polymer or copolymer or resin or monomer) near3 sulfonate).clm.	US-PGPUB	OR	ON	2005/12/01 15:09
L2	90	(cyclohexyl adj acrylate or cyclohexylacrylate).clm.	US-PGPUB	OR	ON	2005/12/01 15:10
L3	84	(phenyl adj acrylate or phenylacrylate or hydroxyphenyl adj acrylate or hydroxyphenyl adj acrylate).clm.	US-PGPUB	OR	ON	2005/12/01 15:10
L4	0	(hydroxycyclohexyl adj acrylate or hydroxycyclohexylacrylate).clm.	US-PGPUB	OR	ON	2005/12/01 15:01
L5	0	(hydroxy\$1cyclohexyl adj acrylate or hydroxy\$1cyclohexylacrylate).clm.	US-PGPUB	OR	ON	2005/12/01 15:01
L6	0	1 and 2	US-PGPUB	OR	ON	2005/12/01 15:02
L7	0	1 and 3	US-PGPUB	OR	ON	2005/12/01 15:02
L8	442	(resist adj composition).clm.	US-PGPUB	OR	ON	2005/12/01 15:02
L9	7179	photoresist.clm.	US-PGPUB	OR	ON	2005/12/01 15:02
L10	1	1 and 8	US-PGPUB	OR	ON	2005/12/01 15:03
L11	1	1 and 9	US-PGPUB	OR	ON	2005/12/01 15:04
L12	1608	430/270.1.ccls. or 430/326.ccls.	US-PGPUB	OR	ON	2005/12/01 15:05
L13	107	526/243.ccls. or 526/287.ccls. or 528/391.ccls.	US-PGPUB	OR	ON	2005/12/01 15:05
L14	1873	526/243.ccls. or 526/287.ccls. or 528/391.ccls.	US-PGPUB; USPAT	OR	ON	2005/12/01 15:05
L15	5992	430/270.1.ccls. or 430/326.ccls.	US-PGPUB; USPAT	OR	ON	2005/12/01 15:05
L16	10	14 and 1	US-PGPUB; USPAT	OR	ON	2005/12/01 15:05
L17	3	15 and 1	US-PGPUB; USPAT	OR	ON	2005/12/01 15:08
L18	10181	(polymer or copolymer or resin or monomer) near3 sulfonate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:10
L19	5813	cyclohexyl adj acrylate or cyclohexylacrylate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:10

Inter
ference

class/
sub-
class

Text.

Text
↓

L20	5953	(phenyl adj acrylate or phenylacrylate or hydroxyphenyl adj acrylate or hydroxyphenyl adj acrylate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:11
L21	121	18 and 19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:23
L22	214	18 and 20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:11
L23	3871	styrene adj sulfonate or pyridinium adj sulfonate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:23
L24	92	21 not 23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:29
L25	154	22 not 23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:24
L26	3513	vinylsulfonate or vinyl adj sulfonate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:29
L27	12	25 and 26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/01 15:30

10/773, 228 (12-28-99 = FD)
 STN Reg file struc. search, Sulfonate monomers, 12/1/05
 claim 2, R9A

L9 ANSWER 1 OF 6 CAPLUS COPYRIGHT 2005 ACS on STN
 AN 2004:753223 CAPLUS
 DN 141:268557
 TI Positive resist composition and method of forming a resist pattern using the same
 IN Sasaki, Tomoŷa
 PA Fuji Photo Film Co., Ltd., Japan
 SO Eur. Pat. Appl., 80 pp.
 CODEN: EPXXDW
 DT Patent
 LA English
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	EP 1457819	A2	20040915	EP 2004-4961	20040303
	EP 1457819	A3	20050622		
	R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR, BG, CZ, EE, HU, PL, SK				
	JP 2004279471	A2	20041007	JP 2003-67010	20030312
PRAI	JP 2003-67010	A	20030312		

AB A pos. photoresist composition comprises (A) a resin comprising specific repeating units and coming to have enhanced solubility in an alkaline developing solution by the action of an acid and (B) a compound generating an acid by the action of actinic rays or a radiation.

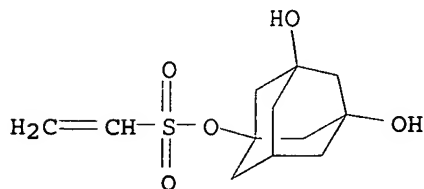
IT 756532-39-5P
 RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
 (pos. photoresist composition for forming resist pattern)

RN 756532-39-5 CAPLUS
 CN Ethenesulfonic acid, 3,5-dihydroxytricyclo[3.3.1.1^{3,7}]dec-1-yl ester, polymer with 1-ethenyl-3,5-bis[1-(ethoxymethoxy)-2,2,2-trifluoro-1-(trifluoromethyl)ethyl]benzene (9CI) (CA INDEX NAME)

CM 1

CRN 677354-87-9

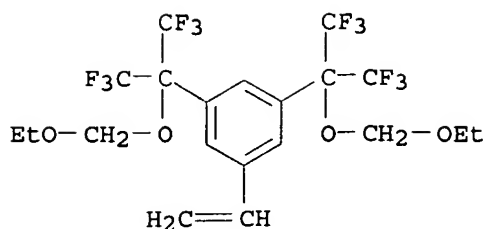
CMF C12 H18 O5 S



CM 2

CRN 585573-40-6

CMF C20 H20 F12 O4



L9 ANSWER 2 OF 6 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2004:291622 CAPLUS

DN 140:329533

TI Positive-working photoresist composition containing specific resin

IN Sasaki, Tomoya; Mizutani, Kazuyoshi; Kanna, Shinichi

PA Fuji Photo Film Co., Ltd., Japan

SO Jpn. Kokai Tokkyo Koho, 83 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2004109834	A2	20040408	JP 2002-275241	20020920
PRAI	JP 2002-275241		20020920		

AB The title composition contains aresin increasing the solubility in an alkali solution

by an acid and an actinic ray- or radiation sensitive acid-generator, wherein the resin has repeating unit [-C(R1)(R2)-C(R3)(-O-L1-[C(C(R21R22R23))(C(R24R25R26))]n-L2-C(OZa)(C(R27R28R29))(C(R30R31R32)))] (r1-3 = H, halo, cyano, alkyl; R21-32 = H, F, alkyl; L1-2 = single bond, 2-valent connecting group; n = 0, 1) and repeating unit containing the structure -[C(R4)(R5)]m-Z1-(X)p (R4-5 = alkyl; Z1 = (p+1)-valent alicyclic hydrocarbon; X = F, Cl, OH< etc.; m = 0, 1; p = integer 1-4). Composition is suitable for exposure beam of ≤160 nm and show good characteristics on development, image formation, dry etching resistance, etc.

IT 677354-89-1P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(resin in pos.-working photoresist composition)

RN 677354-89-1 CAPLUS

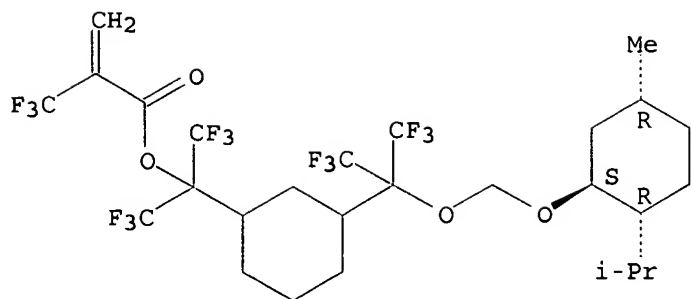
CN 2-Propenoic acid, 2-(trifluoromethyl)-, 2,2,2-trifluoro-1-(trifluoromethyl)-1-[3-[2,2,2-trifluoro-1-[[[(1S,2R,5R)-5-methyl-2-(1-methylethyl)cyclohexyl]oxy]methoxy]-1-(trifluoromethyl)ethyl]cyclohexyl]ethyl ester, polymer with 3,5-dihydroxytricyclo[3.3.1.1^{3,7}]dec-1-yl ethenesulfonate and 4-[[2-(ethenyloxy)ethoxy]methyl]-α,α-bis(trifluoromethyl)tricyclo[3.3.1.1^{3,7}]decane-1-methanol (9CI) (CA INDEX NAME)

CM 1

CRN 677354-88-0

CMF C27 H33 F15 O4

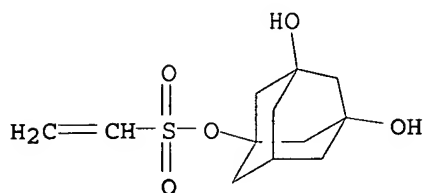
Absolute stereochemistry.



CM 2

CRN 677354-87-9

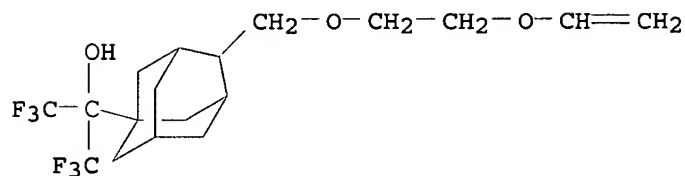
CMF C12 H18 O5 S



CM 3

CRN 677354-86-8

CMF C18 H24 F6 O3



L9 ANSWER 3 OF 6 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2003:658739 CAPLUS

DN 140:33571

TI A new photoresist materials for 157 nm lithography-3: Poly[2-hydroxy-3-pinanyl vinyl sulfonate-co-4-(1,1,1,3,3,3-hexafluoro-2-hydroxypropyl)styrene]

AU Iimori, H.; Ando, S.; Shibasaki, Y.; Ueda, M.; Kishimura, S.; Endo, M.; Sasago, M.

CS Department of Organic and Polymeric Materials, Tokyo Institute of Technology, Graduate School of Science and Engineering, Tokyo, 152-8552, Japan

SO Journal of Photopolymer Science and Technology (2003), 16(4), 601-605
CODEN: JSTEEW; ISSN: 0914-9244

PB Technical Association of Photopolymers, Japan

DT Journal

LA English

AB A new photoresist for 157 nm lithog. is based poly[(2-hydroxy-3-pinanyl vinyl sulfonate)-co-4-(1,1,1,3,3,3-hexafluoro-2-hydroxypropyl)styrene] [poly(VSO3Pina73-co-HFIST27)] and triphenylsulfonium perfluoro-1-

butanesulfonate (TPS-Nf) as a photoacid generator (PAG).

Poly(VSO3Pina-co-HFIST)s were prepared by free radical polymerization of VSO3Pina with HFIST. The photoresist consisting of poly(VSO3Pina73-co-HFIST27) and 4 wt% TPS-Nf showed a sensitivity of 10 mJ cm⁻² and a contrast of 6, when it was exposed to 157 nm laser and developed with 0.6 wt% aqueous tetramethylammonium hydroxide (TMAH) solution at 25 °C. A fine pos. image of 140 nm line and space patterns was printed in a film, which was exposed to 15 mJ cm⁻² by a contact printed mode. The resist film showed an optical d. (OD) value of 3.6 μm⁻¹ at 157 nm wavelength.

IT 479423-09-1P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
(characterization of photoresist for vacuum-UV lithog. based on hydroxypinanylvinyl sulfonate-hexafluorohydroxypropylstyrene copolymer)

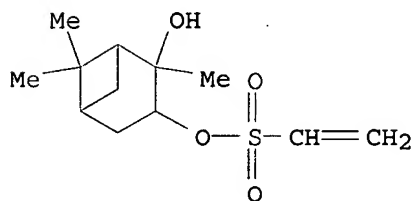
RN 479423-09-1 CAPLUS

CN Ethenesulfonic acid, 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ester, polymer with 4-ethenyl-α,α-bis(trifluoromethyl)benzenemethanol (9CI) (CA INDEX NAME)

CM 1

CRN 479423-01-3

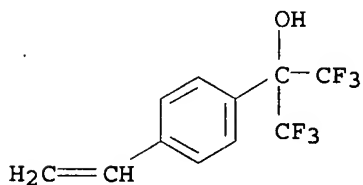
CMF C12 H20 O4 S



CM 2

CRN 2386-82-5

CMF C11 H8 F6 O

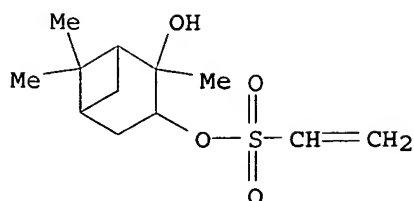


IT 479423-01-3P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)
(copolymn. with hexafluorohydroxypropylstyrene)

RN 479423-01-3 CAPLUS

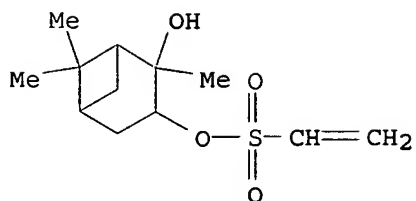
CN Ethenesulfonic acid, 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ester (9CI) (CA INDEX NAME)



RE.CNT 20 THERE ARE 20 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L9 ANSWER 4 OF 6 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2003:242619 CAPLUS
DN 138:278392
TI Photoresist composition for pattern formation in making printed circuit boards
IN Kishimura, Shinji; Endo, Masayuki; Sasago, Masaru; Ueda, Mitsuru; Fujigaya, Tsuyohiko
PA Matsushita Electric Industrial Co., Ltd., Japan
SO PCT Int. Appl., 59 pp.
CODEN: PIXXD2
DT Patent
LA Japanese
FAN.CNT 1

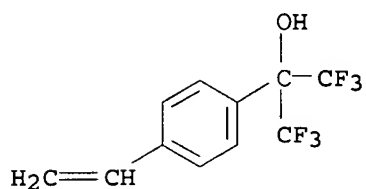
	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	WO 2003025676	A1	20030327	WO 2002-JP9381	20020912
	W: CN, JP, KR, US				
	RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, SK, TR				
	TW 589514	B	20040601	TW 2002-91119405	20020827
	EP 1403711	A1	20040331	EP 2002-765525	20020912
	R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, FI, CY, TR, BG, CZ, EE, SK				
	CN 1524200	A	20040825	CN 2002-802641	20020912
	US 2004029035	A1	20040212	US 2003-415272	20030428
PRAI	JP 2001-277589	A	20010913		
	WO 2002-JP9381	W	20020912		
AB	Title photoresist composition comprises a base resin containing structural repeating unit CH ₂ CR ₁ SO ₃ R ₂ and, other units such as CH ₂ CR ₃ C ₆ H ₄ (CH ₂)mC(CF ₃) ₂ OR ₄ and Q(CH ₂)pC(CF ₃) ₂ OR ₆ (C ₆ H ₄ = p-phenylene; Q = norbornene residue; R ₁ , R ₃ = H, Cl, F, alkyl, fluoroalkyl; R ₂ , R ₄ , R ₆ = H, alkyl, alicyclic group, aromatic group, heterocycle, ester group, ether group; m, p = 0-5) and an acid generator. A pattern-forming method is characterized by exposure to light having wave length <180 nm.				
IT	479423-09-1D, reaction products 503178-58-3 503178-59-4D, reaction products 503178-60-7 503178-64-1 RL: POF (Polymer in formulation); TEM (Technical or engineered material use); USES (Uses) (photoresist composition for pattern formation in making printed circuit boards)				
RN	479423-09-1 CAPLUS				
CN	Ethenesulfonic acid, 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ester, polymer with 4-ethenyl-α,α-bis(trifluoromethyl)benzenemethanol (9CI) (CA INDEX NAME)				
CM	1				
CRN	479423-01-3				
CMF	C12 H20 O4 S				



CM 2

CRN 2386-82-5

CMF C11 H8 F6 O



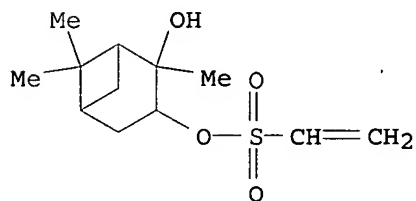
RN 503178-58-3 CAPLUS

CN Ethenesulfonic acid, 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ester, homopolymer (9CI) (CA INDEX NAME)

CM 1

CRN 479423-01-3

CMF C12 H20 O4 S



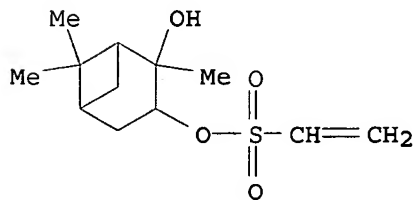
RN 503178-59-4 CAPLUS

CN Ethenesulfonic acid, polymer with 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 479423-01-3

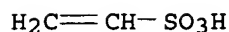
CMF C12 H20 O4 S



CM 2

CRN 1184-84-5

CMF C2 H4 O3 S



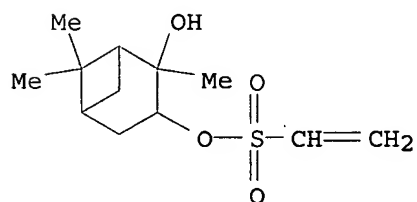
RN 503178-60-7 CAPLUS

CN Carbonic acid, 1,1-dimethylethyl 1-(4-ethenylphenyl)-2,2,2-trifluoro-1-(trifluoromethyl)ethyl ester, polymer with 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 479423-01-3

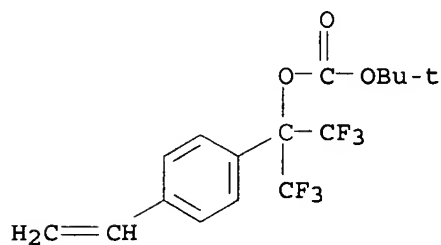
CMF C12 H20 O4 S



CM 2

CRN 143336-93-0

CMF C16 H16 F6 O3



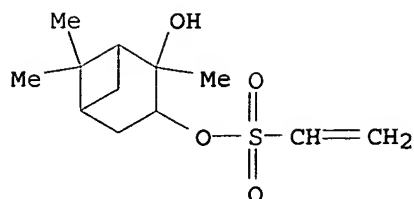
RN 503178-64-1 CAPLUS

CN Carbonic acid, 1,1-dimethylethyl 1-(4-ethenylphenyl)-2,2,2-trifluoro-1-(trifluoromethyl)ethyl ester, polymer with 4-ethenyl- α,α -bis(trifluoromethyl)benzenemethanol and 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 479423-01-3

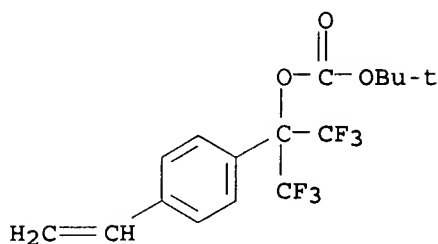
CMF C12 H20 O4 S



CM 2

CRN 143336-93-0

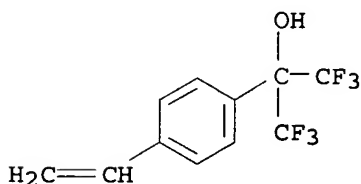
CMF C16 H16 F6 O3



CM 3

CRN 2386-82-5

CMF C11 H8 F6 O



RE.CNT 13 THERE ARE 13 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L9 ANSWER 5 OF 6 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2002:633341 CAPLUS
DN 138:63741
TI A new photoresist material for 157 nm lithography-2
AU Fujigaya, T.; Ando, S.; Shibasaki, Y.; Kishimura, S.; Endo, M.; Sasago, M.; Ueda, M.
CS Department of Organic and Polymeric Materials, Tokyo Institute of Technology, Tokyo, 152-8552, Japan
SO Journal of Photopolymer Science and Technology (2002), 15(4), 643-654
CODEN: JSTEEW; ISSN: 0914-9244
PB Technical Association of Photopolymers, Japan
DT Journal
LA English
AB Time-dependent d. functional theory (TD-DFT) calcns. using the B3LYP hybrid functional suggested that sulfonic acid esters are transparent at around 157 nm region. Based on these findings, poly(vinyl methylsulfonate) [poly(VSO3Me)] was prepared and found to have an extremely low absorbance (Absolute) of 2.2 μm^{-1} at 157 nm. Various vinyl

alkylsulfonates (VSO3R)s were prepared from 2-chloroethanesulfonyl chloride and alc. components in the presence of pyridine, and their radical polymns. were conducted in bulk using 2,2'-azobis(isobutyronitrile) as an initiator. Polymns. of primary and secondary VSO3Rs bearing small alkyl substituents gave homopolymers with high mol. wts. Among them, the Absolute of poly(vinyl 2,2,2-trifluoroethylsulfonate) reached 1.3 μm^{-1} . Various copolymers from vinyl alkylsulfonates and 4-(1,1,1,3,3,3-hexafluoro-2-hydroxypropyl)styrene (HFIST) were also prepared and the Absolute of poly(vinyl 1,1,1,3,3,3-hexafluoroisopropylsulfonate-co-HFIST60) [poly(VSO3iPr6F40-co-HFIST60)] was found to be 2.4 μm^{-1} at 157 nm. The photoresist consisting of partially tert-butoxycarbonyl-protected poly(VSO3iPr6F40-co-HFIST28-co-t-BOCHFIST32) (Absolute 2.6) and an photoacid generator showed the contrast and sensitivity of 10.3 and 5.0 mJ cm^{-2} , resp. Attention: 2-chloroethanesulfonyl chloride, vinyl 2,2,2-trifluoroethylsulfonate and vinyl 1,1,1,3,3,3-hexafluoroisopropylsulfonate are severe eye and skin irritants.

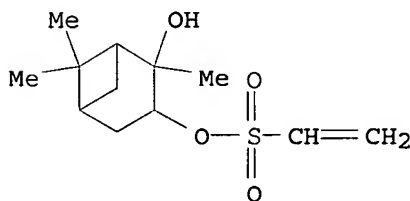
IT 479423-01-3P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)

(copolymn. with hexafluorohydroxypropylstyrene in preparation of polymers for vacuum-UV photoresist applications)

RN 479423-01-3 CAPLUS

CN Ethenesulfonic acid, 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ester (9CI) (CA INDEX NAME)



IT 479423-09-1P

RL: PRP (Properties); SPN (Synthetic preparation); PREP (Preparation) (thermal properties and calcn. of vacuum-UV spectra of vinyl alkylsulfonate-(hexafluorohydroxypropyl)styrene copolymers for photoresist applications)

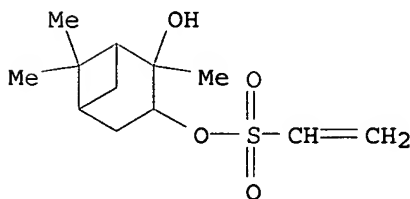
RN 479423-09-1 CAPLUS

CN Ethenesulfonic acid, 2-hydroxy-2,6,6-trimethylbicyclo[3.1.1]hept-3-yl ester, polymer with 4-ethenyl- α,α -bis(trifluoromethyl)benzenemethanol (9CI) (CA INDEX NAME)

CM 1

CRN 479423-01-3

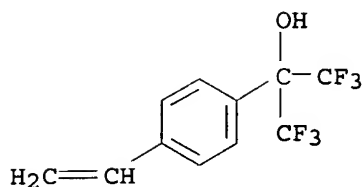
CMF C12 H20 O4 S



CM 2

CRN 2386-82-5

CMF C11 H8 F6 O



RE.CNT 38 THERE ARE 38 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L9 ANSWER 6 OF 6 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2000:585594 CAPLUS
DN 133:200844
TI Positive-working photoresist composition containing polymer having
sulfonate group
IN Sato, Kenichiro; Kodama, Kunihiro; Aogo, Toshiaki
PA Fuji Photo Film Co., Ltd., Japan
SO Jpn. Kokai Tokkyo Koho, 47 pp.
CODEN: JKXXAF

DT Patent
LA Japanese

FAN.CNT 2

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2000231194	A2	20000822	JP 1999-240600	19990826
	KR 2000047927	A	20000725	KR 1999-55067	19991206
	US 6576392	B1	20030610	US 1999-456827	19991206
PRAI	JP 1998-347193	A	19981207		
	JP 1999-30209	A	19990208		
	JP 1999-240600	A	19990826		

AB The title photoresist composition contains a compound which generates an acid
by

irradiation with activating ray or radiation and a resin which contains a repeating unit having SO₂OR group [R = alkyl, cycloalkyl, alkenyl (these groups may be substituted)] and of which the dissoln. rate to alkaline developing solns. increases by the action of acid. The composition shows high sensitivity toward far UV rays, especially KrF or ArF excimer laser beams and good developability and provides high resolution patterns with improved coarse-dense dependence.

IT 289040-37-5D, hydrolyzed

RL: TEM (Technical or engineered material use); USES (Uses)

(photoresist composition containing alkali-soluble polymer with sulfonate group)

RN 289040-37-5 CAPLUS

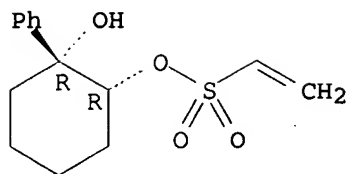
CN Ethenesulfonic acid, (1R,2R)-2-hydroxy-2-phenylcyclohexyl ester, rel-, polymer with 1-[1-(1,1-dimethylethoxy)ethoxy]-4-ethenylbenzene and 4-ethenylphenol (9CI) (CA INDEX NAME)

CM 1

CRN 289040-36-4

CMF C14 H18 O4 S

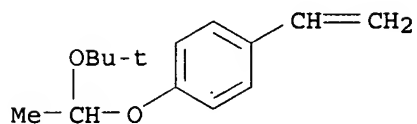
Relative stereochemistry.



CM 2

CRN 169811-45-4

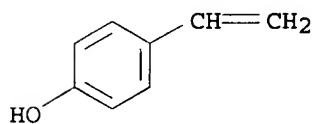
CMF C14 H20 O2



CM 3

CRN 2628-17-3

CMF C8 H8 O



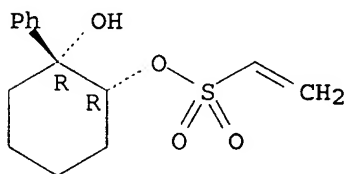
IT 289040-36-4P

RL: PNU (Preparation, unclassified); RCT (Reactant); PREP (Preparation);
 RACT (Reactant or reagent)
 (preparation and polymerization of)

RN 289040-36-4 CAPLUS

CN Ethenesulfonic acid, (1R,2R)-2-hydroxy-2-phenylcyclohexyl ester, rel-
 (9CI) (CA INDEX NAME)

Relative stereochemistry.



=>

L10 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN
 AN 1993:682319 CAPLUS
 DN 119:282319
 TI Ink ribbon and printing paper for thermal recording
 IN Shinozaki, Kenji
 PA Sony Corp., Japan
 SO Jpn. Kokai Tokkyo Koho, 12 pp.
 CODEN: JKXXAF
 DT Patent
 LA Japanese
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 05112080	A2	19930507	JP 1991-303977	19911023
PRAI	JP 1991-303977		19911023		

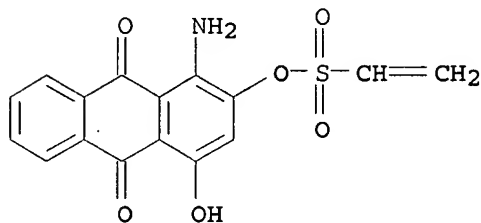
AB The method involves transferring a dye containing I (X = Cl, F; Y = Cl, OMe, NHR, SO₂, CH:CH₂; R = alkyl), II (X₁, Y₁ = Cl, F, SO₂, Me; Z = Cl, Me, F), and/or III (X₂, Y₂ = Cl, F) to a receiving layer with an OH- or NH₂-containing resin by applying a thermal energy and fixing. The ribbon contains a substrate coated with an ink layer containing the dye. The paper contains a receiving layer, fixed by the dye, containing the resin and an electrolyte on a substrate.

IT 151453-30-4

RL: DEV (Device component use); USES (Uses)
 (ink ribbon containing, for thermal-transfer recording)

RN 151453-30-4 CAPLUS

CN Ethenesulfonic acid, 1-amino-9,10-dihydro-4-hydroxy-9,10-dioxo-2-anthracenyl ester (9CI) (CA INDEX NAME)



=>

=> d bib ab hitstr

L20 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2004:963502 CAPLUS

DN 141:417925

TI Positive-working vacuum-UV photoresist composition and patterning method using the same

IN Sasaki, Tomoya

PA Fuji Photo Film Co., Ltd., Japan

SO Jpn. Kokai Tokkyo Koho, 99 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2004318046	A2	20041111	JP 2003-293188	20030813
PRAI	JP 2003-94329	A	20030331		

AB Disclosed is the pos.-working vacuum-UV photoresist composition especially suited for

a F2 excimer laser (157 nm) comprising (a) a resin having a repeating unit FR0C-CFR1, FR0C-CF(OR2), and/or F(R3O)C-CFR4 (R0,1 = H, F, alkyl, cycloalkyl, etc.; R2-4 = alkyl, cycloalkyl, etc.), and (b) a photoacid.

IT 791849-10-0

RL: PRP (Properties); TEM (Technical or engineered material use); USES (Uses)

(pos.-working vacuum-UV photoresist composition containing fluoropolymer and photoacid)

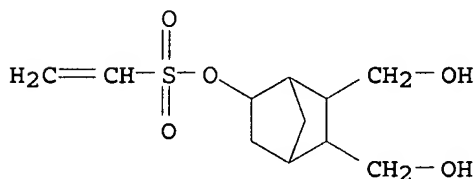
RN 791849-10-0 CAPLUS

CN Ethenesulfonic acid, 5,6-bis(hydroxymethyl)bicyclo[2.2.1]hept-2-yl ester, polymer with 5-[2-(ethoxymethoxy)-3,3,3-trifluoro-2-(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-ene and 1,1,2,3,3,3-hexafluoro-1-propene (9CI) (CA INDEX NAME)

CM 1

CRN 791849-09-7

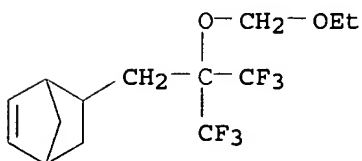
CMF C11 H18 O5 S



CM 2

CRN 328114-61-0

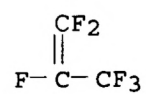
CMF C14 H18 F6 O2



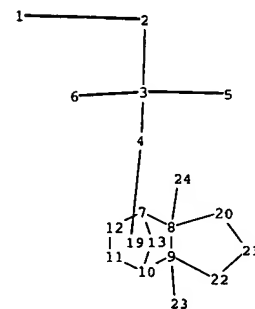
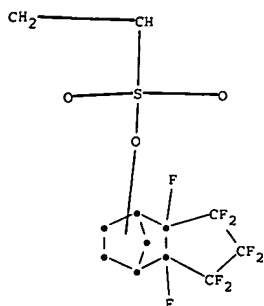
CM 3

CRN 116-15-4

CMF C3 F6



=>



chain nodes :

1 2 3 4 5 6 15 17 23 24

ring nodes :

7 8 9 10 11 12 13 20 21 22

chain bonds :

1-2 2-3 3-4 3-5 3-6 8-24 9-23 15-17

ring bonds :

7-8 7-12 7-13 8-9 8-20 9-10 9-22 10-11 10-13 11-12 20-21 21-22

exact/norm bonds :

2-3 3-4 3-5 3-6 7-8 7-12 7-13 8-9 8-20 9-10 9-22 10-11 10-13
11-12 15-17 20-21 21-22

exact bonds :

1-2 8-24 9-23

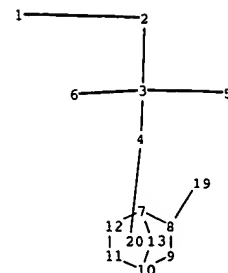
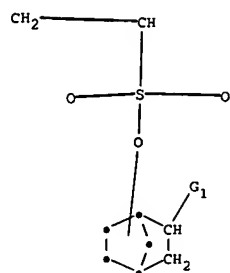
G1:CF2,CF3,[*1]

Match level :

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
10:Atom 11:Atom 12:Atom 13:Atom 15:CLASS 17:CLASS 19:CLASS 20:CLASS
21:Atom 22:Atom 23:CLASS 24:CLASS

Element Count :

Node 15: Limited
C,C1-20



chain nodes :

1 2 3 4 5 6 15 17 19

ring nodes :

7 8 9 10 11 12 13

chain bonds :

1-2 2-3 3-4 3-5 3-6 8-19 15-17

ring bonds :

7-8 7-12 7-13 8-9 9-10 10-11 10-13 11-12

exact/norm bonds :

2-3 3-4 3-5 3-6 7-8 7-12 7-13 8-9 8-19 9-10 10-11 10-13 11-12
15-17

exact bonds :

1-2

G1:CF2,CF3,[*1]

Match level :

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
10:Atom 11:Atom 12:Atom 13:Atom 15:CLASS 17:CLASS 19:CLASS 20:CLASS

Element Count :

Node 15: Limited
C,C1-20

(FILE 'HOME' ENTERED AT 13:11:30 ON 01 DEC 2005)

FILE 'REGISTRY' ENTERED AT 13:11:35 ON 01 DEC 2005

L1 STRUCTURE UPLOADED
L2 STRUCTURE UPLOADED
L3 STRUCTURE UPLOADED
L4 STRUCTURE UPLOADED
L5 0 S L1 FULL
L6 0 S L2 FULL
L7 11 S L3 FULL
L8 2 S L4 FULL

FILE 'CAPLUS' ENTERED AT 13:16:14 ON 01 DEC 2005

L9 6 S L7
L10 1 S L8

FILE 'REGISTRY' ENTERED AT 13:19:01 ON 01 DEC 2005

L11 STRUCTURE UPLOADED
L12 STRUCTURE UPLOADED
L13 STRUCTURE UPLOADED
L14 STRUCTURE UPLOADED
L15 STRUCTURE UPLOADED
L16 0 S L11 FULL
L17 0 S L12 FULL
L18 0 S L13 FULL
L19 2 S L14 FULL

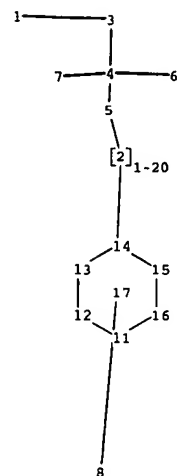
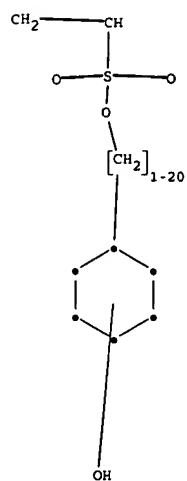
FILE 'CAPLUS' ENTERED AT 13:22:01 ON 01 DEC 2005

L20 1 S L19

FILE 'REGISTRY' ENTERED AT 13:32:50 ON 01 DEC 2005

L21 STRUCTURE UPLOADED
L22 STRUCTURE UPLOADED
L23 0 S L21 FULL
L24 0 S L22 FULL

=>



chain nodes :

1 2 3 4 5 6 7 8

ring nodes :

11 12 13 14 15 16

chain bonds :

1-3 2-5 2-14 3-4 4-5 4-6 4-7

ring bonds :

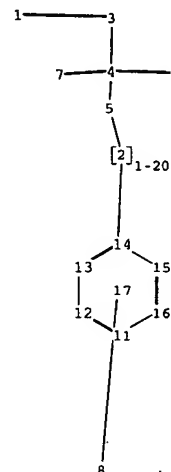
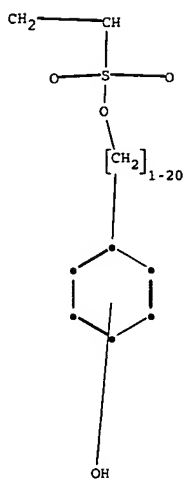
11-12 11-16 12-13 13-14 14-15 15-16

exact bonds :

1-3 2-5 2-14 3-4 4-5 4-6 4-7 11-12 11-16 12-13 13-14 14-15
15-16

Match level :

1:CLASS 2:CLASS 3:CLASS 4:CLASS 5:CLASS 6:CLASS 7:CLASS 8:CLASS
11:Atom 12:Atom 13:Atom 14:Atom 15:Atom 16:Atom 17:CLASS



chain nodes :

1 2 3 4 5 6 7 8

ring nodes :

11 12 13 14 15 16

chain bonds :

1-3 2-5 2-14 3-4 4-5 4-6 4-7

ring bonds :

11-12 11-16 12-13 13-14 14-15 15-16

exact bonds :

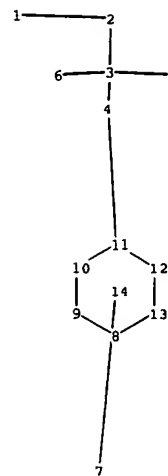
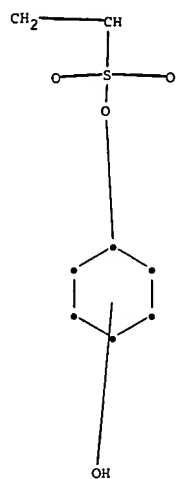
1-3 2-5 2-14 3-4 4-5 4-6 4-7

normalized bonds :

11-12 11-16 12-13 13-14 14-15 15-16

Match level :

1:CLASS	2:CLASS	3:CLASS	4:CLASS	5:CLASS	6:CLASS	7:CLASS	8:CLASS
11:Atom	12:Atom	13:Atom	14:Atom	15:Atom	16:Atom	17:CLASS	



chain nodes :

1 2 3 4 5 6 7

ring nodes :

8 9 10 11 12 13

chain bonds :

1-2 2-3 3-4 3-5 3-6 4-11

ring bonds :

8-9 8-13 9-10 10-11 11-12 12-13

exact/norm bonds :

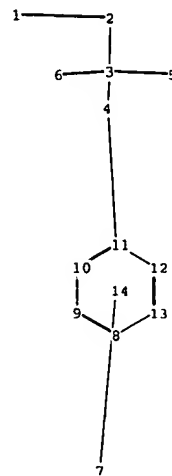
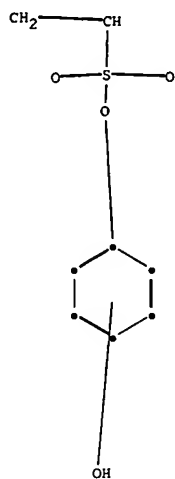
4-11

exact bonds :

1-2 2-3 3-4 3-5 3-6 8-9 8-13 9-10 10-11 11-12 12-13

Match level :

1:CLASS 2:CLASS 3:CLASS 4:CLASS 5:CLASS 6:CLASS 7:CLASS 8:Atom
9:Atom 10:Atom 11:Atom 12:Atom 13:Atom 14:CLASS



chain nodes :

1 2 3 4 5 6 7

ring nodes :

8 9 10 11 12 13

chain bonds :

1-2 2-3 3-4 3-5 3-6 4-11

ring bonds :

8-9 8-13 9-10 10-11 11-12 12-13

exact/norm bonds :

4-11

exact bonds :

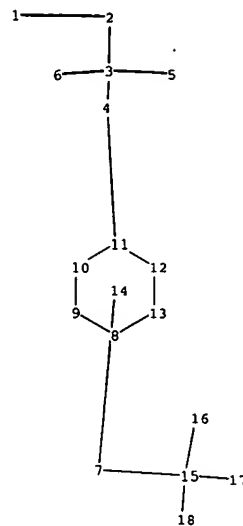
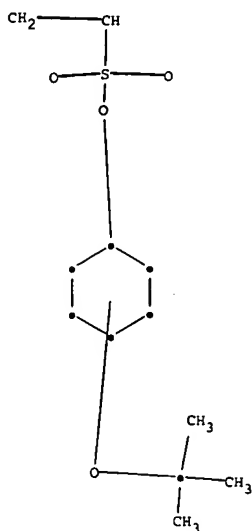
1-2 2-3 3-4 3-5 3-6

normalized bonds :

8-9 8-13 9-10 10-11 11-12 12-13

Match level :

1:CLASS 2:CLASS 3:CLASS 4:CLASS 5:CLASS 6:CLASS 7:CLASS 8:Atom
9:Atom 10:Atom 11:Atom 12:Atom 13:Atom 14:CLASS



chain nodes :

1 2 3 4 5 6 7 15 16 17 18

ring nodes :

8 9 10 11 12 13

chain bonds :

1-2 2-3 3-4 3-5 3-6 4-11 7-15 15-16 15-17 15-18

ring bonds :

8-9 8-13 9-10 10-11 11-12 12-13

exact/norm bonds :

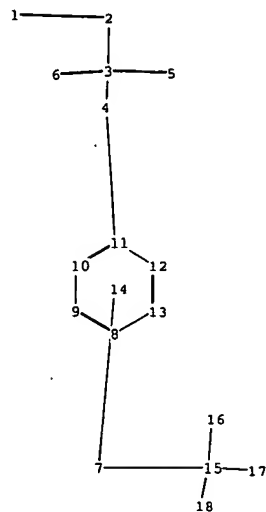
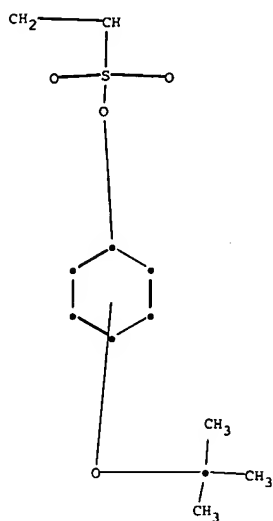
7-15

exact bonds :

1-2 2-3 3-4 3-5 3-6 4-11 8-9 8-13 9-10 10-11 11-12 12-13 15-16
15-17 15-18

Match level :

1:CLASS 2:CLASS 3:CLASS 4:CLASS 5:CLASS 6:CLASS 7:CLASS 8:Atom
9:Atom 10:Atom 11:Atom 12:Atom 13:Atom 14:CLASS 15:CLASS 16:CLASS
17:CLASS 18:CLASS



chain nodes :

1 2 3 4 5 6 7 15 16 17 18

ring nodes :

8 9 10 11 12 13

chain bonds :

1-2 2-3 3-4 3-5 3-6 4-11 7-15 15-16 15-17 15-18

ring bonds :

8-9 8-13 9-10 10-11 11-12 12-13

exact/norm bonds :

4-11 7-15

exact bonds :

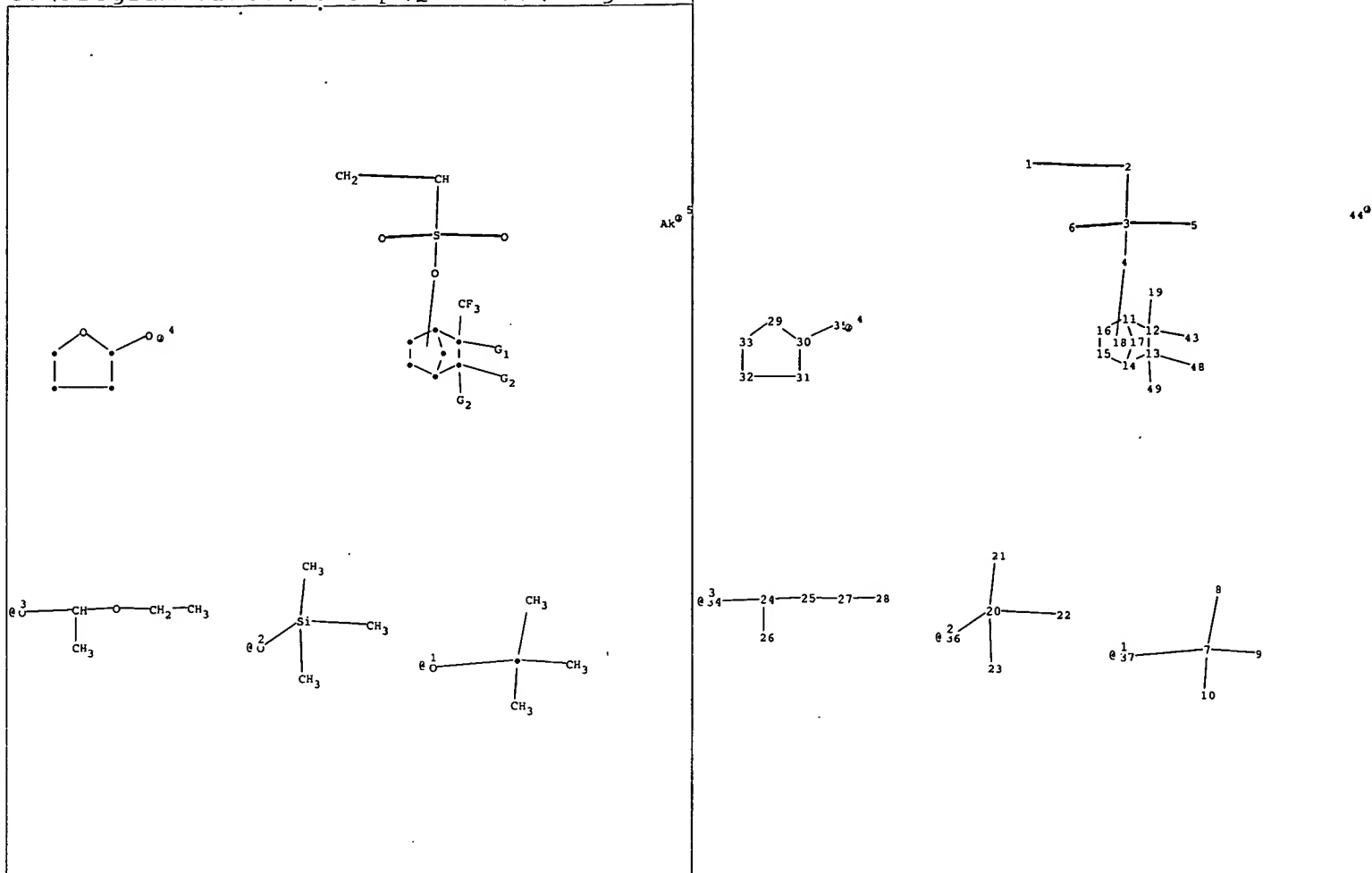
1-2 2-3 3-4 3-5 3-6 15-16 15-17 15-18

normalized bonds :

8-9 8-13 9-10 10-11 11-12 12-13

Match level :

1:CLASS 2:CLASS 3:CLASS 4:CLASS 5:CLASS 6:CLASS 7:CLASS 8:Atom
 9:Atom 10:Atom 11:Atom 12:Atom 13:Atom 14:CLASS 15:CLASS 16:CLASS
 17:CLASS 18:CLASS



chain nodes :

1 2 3 4 5 6 7 8 9 10 19 20 21 22 23 24 25 26 27 28 34
35 36 37 43 44 48 49

ring nodes :

11 12 13 14 15 16 17 29 30 31 32 33

chain bonds :

1-2 2-3 3-4 3-5 3-6 7-10 7-8 7-9 7-37 12-19 12-43 13-48 13-49
20-21 20-22 20-23 20-36 24-25 24-26 24-34 25-27 27-28 30-35

ring bonds :

11-12 11-16 11-17 12-13 13-14 14-15 14-17 15-16 29-30 29-33 30-31
31-32 32-33

exact/norm bonds :

2-3 3-4 3-5 3-6 7-37 11-12 11-16 11-17 12-13 12-43 13-14 13-48
13-49 14-15 14-17 15-16 24-25 24-34 29-30 29-33 30-31 30-35 31-32
32-33

exact bonds :

1-2 7-10 7-8 7-9 12-19 20-21 20-22 20-23 20-36 24-26 25-27 27-28

G1:OH, [*1], [*2], [*3], [*4]

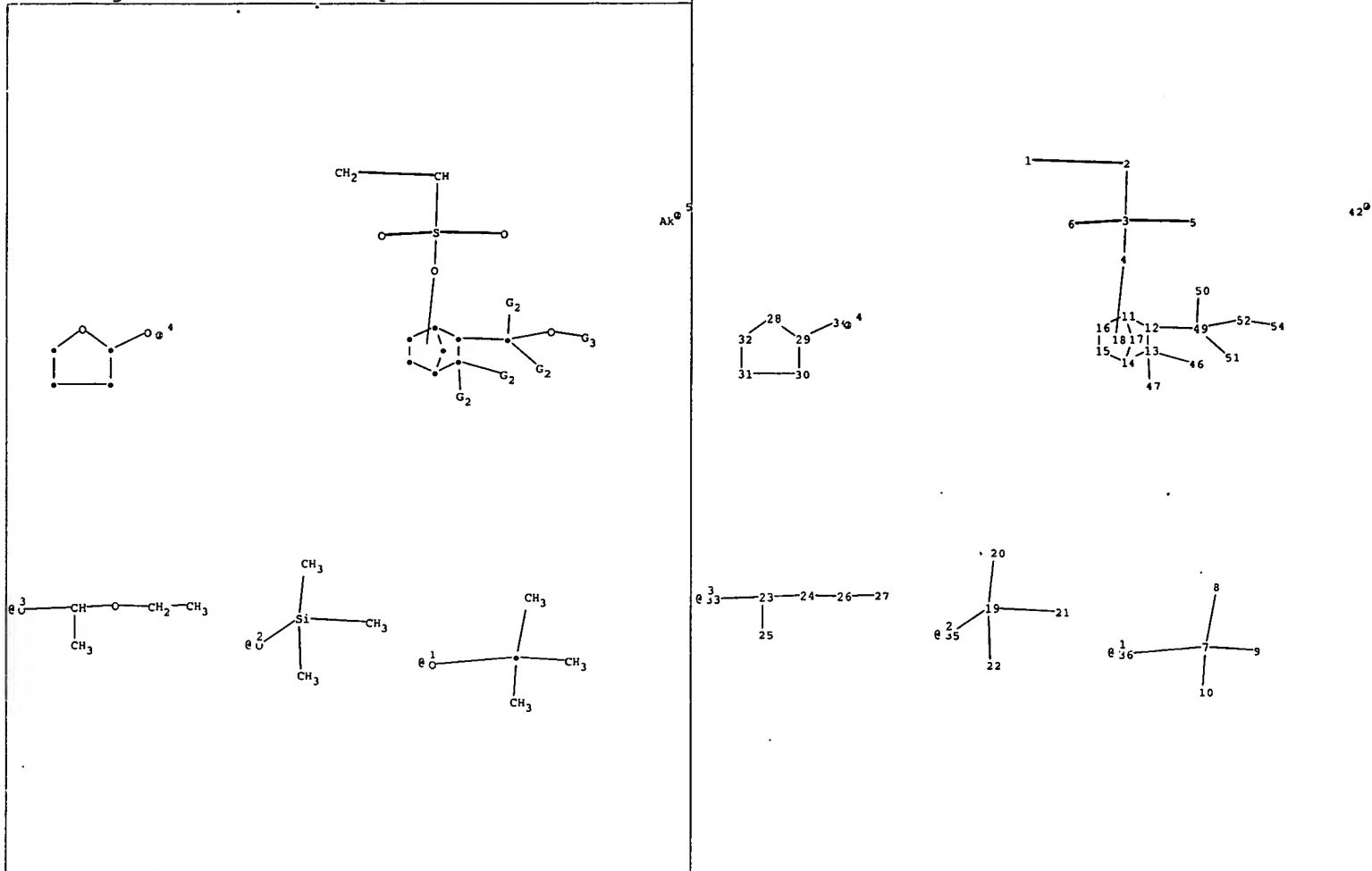
G2:H, F, CF2, CF3, [*5]

Match level :

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
10:Atom 11:Atom 12:Atom 13:Atom 14:Atom 15:Atom 16:Atom 17:Atom
18:Atom 19:Atom 20:CLASS 21:Atom 22:Atom 23:Atom 24:Atom 25:Atom
26:Atom 27:Atom 28:Atom 29:Atom 30:Atom 31:Atom 32:Atom 33:Atom
34:Atom 35:Atom 36:Atom 37:Atom 43:Atom 44:Atom 48:CLASS 49:CLASS

Element Count :

Node 44: Limited
C, C1-20



chain nodes :

1 2 3 4 5 6 7 8 9 10 19 20 21 22 23 24 25 26 27 33 34
35 36 42 46 47 49 50 51 52 54

ring nodes :

11 12 13 14 15 16 17 28 29 30 31 32

chain bonds :

1-2 2-3 3-4 3-5 3-6 7-10 7-8 7-9 7-36 12-49 13-46 13-47 19-20
19-21 19-22 19-35 23-24 23-25 23-33 24-26 26-27 29-34 49-50 49-51
49-52 52-54

ring bonds :

11-12 11-16 11-17 12-13 13-14 14-15 14-17 15-16 28-29 28-32 29-30
30-31 31-32

exact/norm bonds :

2-3 3-4 3-5 3-6 7-36 11-12 11-16 11-17 12-13 13-14 13-46 13-47
14-15 14-17 15-16 23-24 23-33 28-29 28-32 29-30 29-34 30-31 31-32
49-50 49-51 49-52 52-54

exact bonds :

1-2 7-10 7-8 7-9 12-49 19-20 19-21 19-22 19-35 23-25 24-26 26-27

G1:OH, [*1], [*2], [*3], [*4]

G2:H, F, CF2, CF3, [*5]

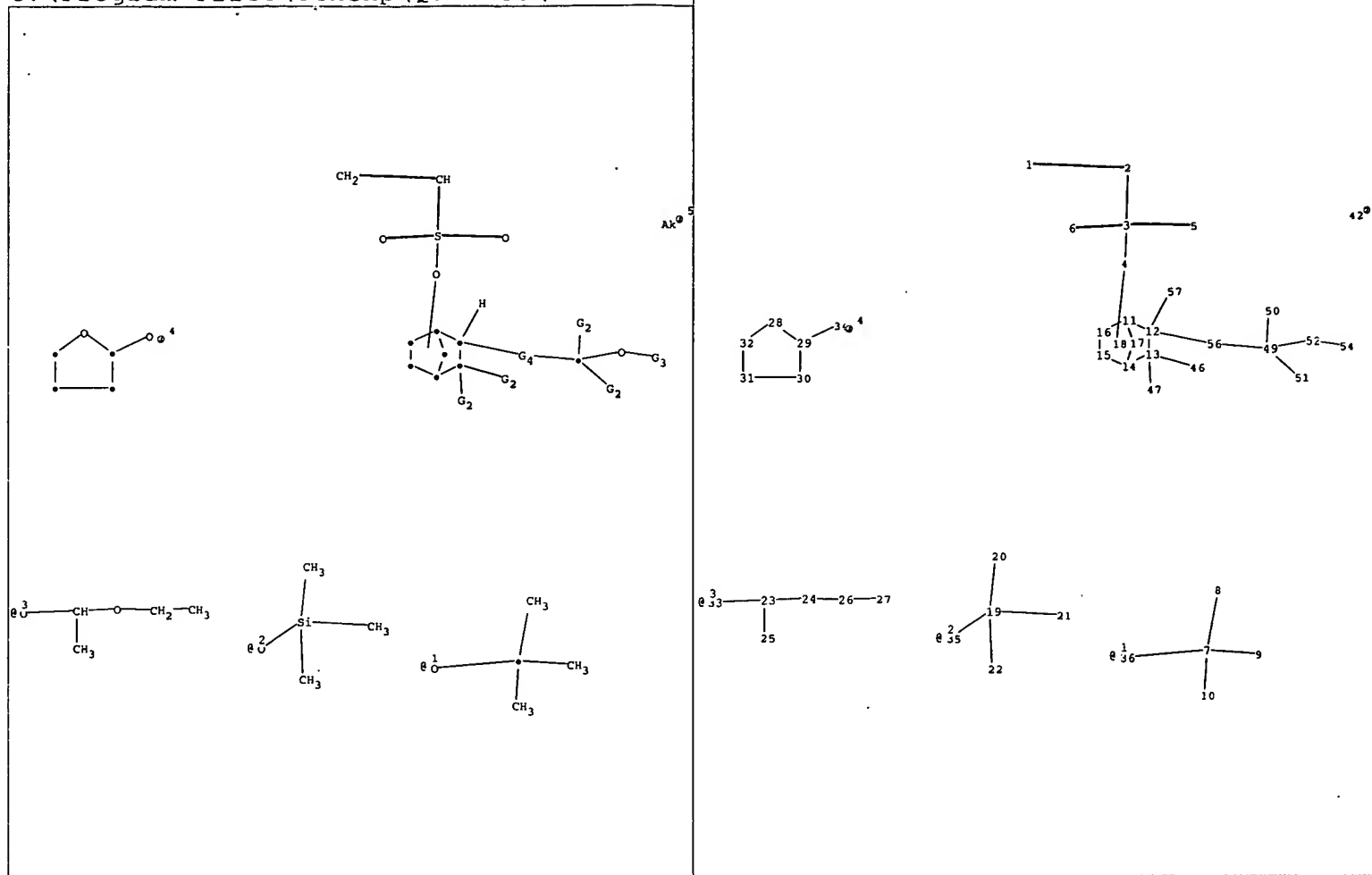
G3:H, [*1], [*2], [*3], [*4]

Match level :

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
10:Atom 11:Atom 12:Atom 13:Atom 14:Atom 15:Atom 16:Atom 17:Atom
18:Atom 19:CLASS 20:Atom 21:Atom 22:Atom 23:Atom 24:Atom 25:Atom
26:Atom 27:Atom 28:Atom 29:Atom 30:Atom 31:Atom 32:Atom 33:Atom
34:Atom 35:Atom 36:Atom 42:Atom 46:CLASS 47:CLASS 49:CLASS 50:CLASS
51:CLASS 52:CLASS 54:CLASS

Element Count :

Node 42: Limited
C,C1-20



chain nodes :

1 2 3 4 5 6 7 8 9 10 19 20 21 22 23 24 25 26 27 33 34
35 36 42 46 47 49 50 51 52 54 56 57

ring nodes :

11 12 13 14 15 16 17 28 29 30 31 32

chain bonds :

1-2 2-3 3-4 3-5 3-6 7-10 7-8 7-9 7-36 12-56 12-57 13-46 13-47
19-20 19-21 19-22 19-35 23-24 23-25 23-33 24-26 26-27 29-34 49-52
49-50 49-51 49-56 52-54

ring bonds :

11-12 11-16 11-17 12-13 13-14 14-15 14-17 15-16 28-29 28-32 29-30
30-31 31-32

exact/norm bonds :

2-3 3-4 3-5 3-6 7-36 11-12 11-16 11-17 12-13 12-56 13-14 13-46
13-47 14-15 14-17 15-16 23-24 23-33 28-29 28-32 29-30 29-34 30-31
31-32 49-52 49-50 49-51 49-56 52-54

exact bonds :

1-2 7-10 7-8 7-9 12-57 19-20 19-21 19-22 19-35 23-25 24-26 26-27

G1:OH, [*1], [*2], [*3], [*4]

G2:H, F, CF2, CF3, [*5]

G3:H, [*1], [*2], [*3], [*4]

G4:CF2, CF3, [*5]

Match level :

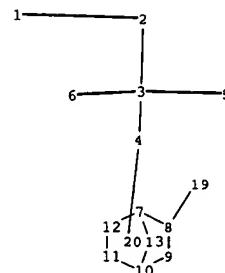
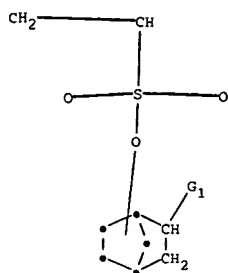
1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
10:Atom 11:Atom 12:Atom 13:Atom 14:Atom 15:Atom 16:Atom 17:Atom
18:Atom 19:CLASS 20:Atom 21:Atom 22:Atom 23:Atom 24:Atom 25:Atom
26:Atom 27:Atom 28:Atom 29:Atom 30:Atom 31:Atom 32:Atom 33:Atom
34:Atom 35:Atom 36:Atom 42:Atom 46:CLASS 47:CLASS 49:CLASS 50:CLASS
51:CLASS

52:CLASS 54:CLASS 56:CLASS 57:CLASS

Element Count :

Node 42: Limited

C,C1-20



chain nodes :

1 2 3 4 5 6 15 17 19

ring nodes :

7 8 9 10 11 12 13

chain bonds :

1-2 2-3 3-4 3-5 3-6 8-19 15-17

ring bonds :

7-8 7-12 7-13 8-9 9-10 10-11 10-13 11-12

exact/norm bonds :

2-3 3-4 3-5 3-6 7-8 7-12 7-13 8-9 8-19 9-10 10-11 10-13 11-12
15-17

exact bonds :

1-2

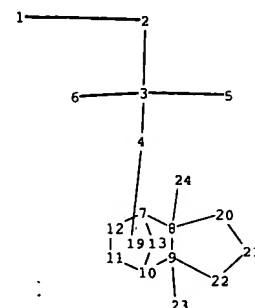
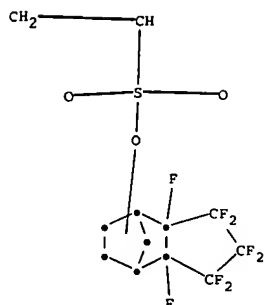
G1:CF2,CF3, [*1]

Match level :

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
10:Atom 11:Atom 12:Atom 13:Atom 15:CLASS 17:CLASS 19:CLASS 20:CLASS

Element Count :

Node 15: Limited
C,C1-20



chain nodes :

1 2 3 4 5 6 15 17 23 24

ring nodes :

7 8 9 10 11 12 13 20 21 22

chain bonds :

1-2 2-3 3-4 3-5 3-6 8-24 9-23 15-17

ring bonds :

7-8 7-12 7-13 8-9 8-20 9-10 9-22 10-11 10-13 11-12 20-21 21-22

exact/norm bonds :

2-3 3-4 3-5 3-6 7-8 7-12 7-13 8-9 8-20 9-10 9-22 10-11 10-13

11-12 15-17 20-21 21-22

exact bonds :

1-2 8-24 9-23

G1:CF2,CF3,[*1]

Match level :

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom
 10:Atom 11:Atom 12:Atom 13:Atom 15:CLASS 17:CLASS 19:CLASS 20:CLASS
 21:Atom 22:Atom 23:CLASS 24:CLASS

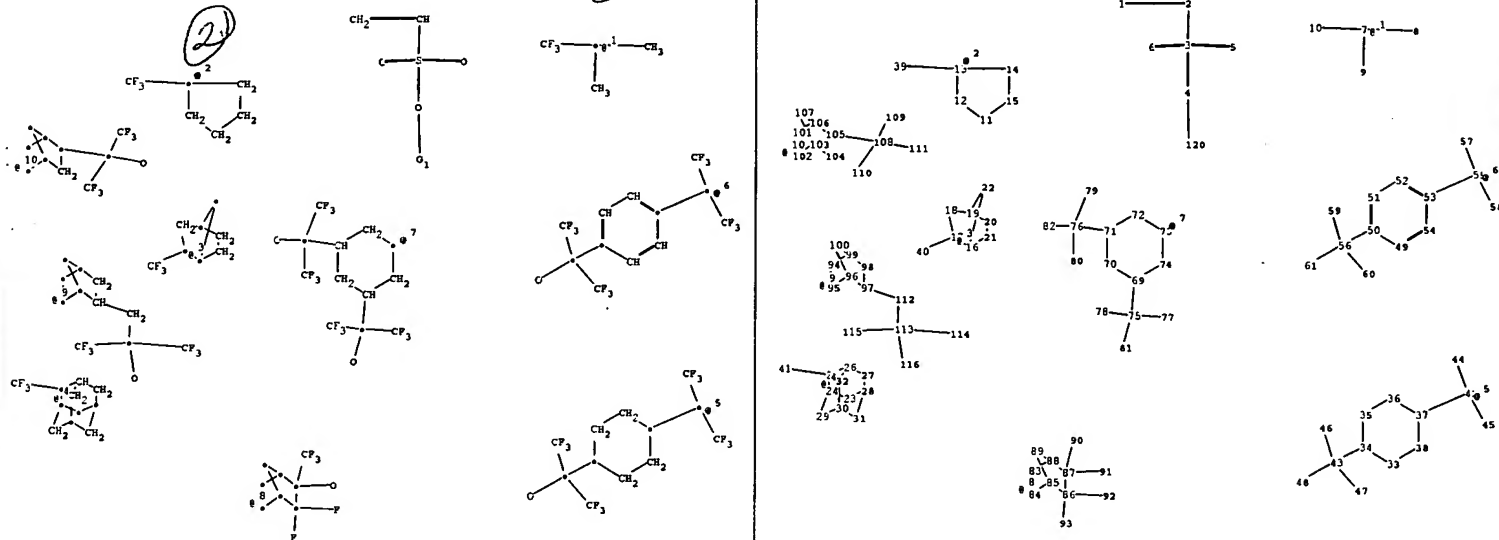
Element Count :

Node 15: Limited

C,C1-20

Sulfonate : claim 5
monomers

①



chain nodes :

1 2 3 4 5 6 7 8 9 10 39 40 41 42 43 44 45 46 47 48 55
56 57 58 59 60 61 75 76 77 78 79 80 81 82 90 91 92 93 108
109 110 111 112 113 114 115 116 120

ring nodes :

11 12 13 14 15 16 17 18 19 20 21 22 23 24 25 26 27 28 29
30 31 32 33 34 35 36 37 38 49 50 51 52 53 54 69 70 71 72
73 74 83 84 85 86 87 88 89 94 95 96 97 98 99 100 101 102
103 104 105 106 107

chain bonds :

1-2 2-3 3-4 3-5 3-6 4-120 7-10 7-8 7-9 13-39 17-40 25-41 34-43
37-42 42-44 42-45 43-46 43-47 43-48 50-56 53-55 55-57 55-58 56-59
56-60 56-61 69-75 71-76 75-77 75-78 75-81 76-79 76-80 76-82 86-92
86-93 87-90 87-91 97-112 105-108 108-109 108-110 108-111 112-113
113-114 113-115 113-116

ring bonds :

11-12 11-15 12-13 13-14 14-15 16-17 16-21 16-22 17-18 18-19 19-20
19-22 20-21 23-24 23-28 24-25 24-29 25-26 26-27 26-32 27-28 28-31
29-30 30-31 30-32 33-34 33-38 34-35 35-36 36-37 37-38 49-50 49-54
50-51 51-52 52-53 53-54 69-70 69-74 70-71 71-72 72-73 73-74 83-84
83-88 84-85 85-86 85-89 86-87 87-88 88-89 94-95 94-99 95-96 96-97
96-100 97-98 98-99 99-100 101-102 101-106 102-103 103-104 103-107
104-105 105-106 106-107

exact/norm bonds :

2-3 3-4 3-5 3-6 4-120 11-12 11-15 12-13 13-14 14-15 16-17 16-21
16-22 17-18 18-19 19-20 19-22 20-21 23-24 23-28 24-25 24-29 25-26
26-27 26-32 27-28 28-31 29-30 30-31 30-32 33-34 33-38 34-35 35-36
36-37 37-38 43-48 56-61 69-70 69-74 70-71 71-72 72-73 73-74 75-81
76-82 83-84 83-88 84-85 85-86 85-89 86-87 87-88 87-91 88-89 94-95
94-99 95-96 96-97 96-100 97-98 98-99 99-100 101-102 101-106
102-103 103-104 103-107 104-105 105-106 106-107 108-111 113-116

exact bonds :

1-2 7-10 7-8 7-9 13-39 17-40 25-41 34-43 37-42 42-44 42-45 43-46
43-47 50-56 53-55 55-57 55-58 56-59 56-60 69-75 71-76 75-77 75-78
76-79

. 76-80 86-92 86-93 87-90 97-112 105-108 108-109 108-110
112-113 113-114 113-115
normalized bonds :
49-50 49-54 50-51 51-52 52-53 53-54

G1:[*1],[*2],[*3],[*4],[*5],[*6],[*7],[*8],[*9],[*10]

Match level :

1:Atom	2:Atom	3:Atom	4:Atom	5:Atom	6:Atom	7:Atom	8:Atom	9:Atom
10:Atom	11:Atom	12:Atom	13:Atom	14:Atom	15:Atom	16:Atom	17:Atom	
18:Atom	19:Atom	20:Atom	21:Atom	22:Atom	23:Atom	24:Atom	25:Atom	
26:Atom	27:Atom	28:Atom	29:Atom	30:Atom	31:Atom	32:Atom	33:Atom	
34:Atom	35:Atom	36:Atom	37:Atom	38:Atom	39:Atom	40:Atom	41:Atom	
42:Atom	43:Atom	44:Atom	45:Atom	46:Atom	47:Atom	48:Atom	49:Atom	
50:Atom	51:Atom	52:Atom	53:Atom	54:Atom	55:Atom	56:Atom	57:Atom	
58:CLASS	59:CLASS	60:CLASS	61:CLASS	69:CLASS	70:CLASS	71:CLASS		
72:CLASS	73:CLASS	74:CLASS	75:CLASS	76:CLASS	77:CLASS	78:CLASS		
79:CLASS	80:CLASS	81:CLASS	82:CLASS	83:CLASS	84:CLASS	85:CLASS		
86:CLASS	87:CLASS	88:CLASS	89:CLASS	90:CLASS	91:CLASS	92:CLASS		
93:CLASS	94:CLASS	95:CLASS	96:CLASS	97:CLASS	98:CLASS	99:CLASS		
100:CLASS	101:Atom	102:Atom	103:Atom	104:Atom	105:Atom	106:Atom		
107:Atom	108:CLASS	109:CLASS	110:CLASS	111:CLASS	112:CLASS	113:CLASS		
114:CLASS	115:CLASS	116:CLASS	120:CLASS					

L3 ANSWER 1 OF 5 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2004:652512 CAPLUS

DN 141:197360

TI Sulfonates, polymers, resist compositions and patterning process

IN Harada, Yuji; Hatakeyama, Jun; Kawai, Yoshio; Sasago, Masaru; Endo, Masayuki; Kishimura, Shinji; Maeda, Kazuhiko; Komoriya, Haruhiko; Miyazawa, Satoru

PA Japan

SO U.S. Pat. Appl. Publ., 26 pp.

CODEN: USXXCO

DT Patent

LA English

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2004157156	A1	20040812	US 2004-773340	20040209
	JP 2004244436	A2	20040902	JP 2003-32584	20030210
PRAI	JP 2003-32584	A	20030210		

AB A sulfonate compound having formula I (R1-3 = H, F, C1-20 alkyl or fluoroalkyl; at least one of R1-3 contains F) is novel. A polymer comprising units derived from the sulfonate compound is used as a base resin to formulate a resist composition which is sensitive to high-energy radiation, maintains high transparency at a wavelength of up to 200 nm, and has improved alkali dissoln. contrast and plasma etching resistance.

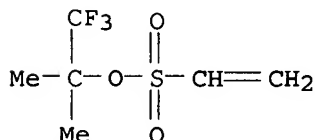
IT 737765-55-8P 737765-56-9P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)

(preparation of sulfonates, polymers for resist compns. and patterning process)

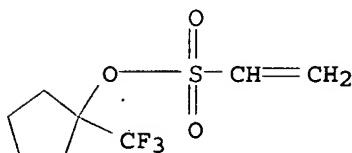
RN 737765-55-8 CAPLUS

CN Ethenesulfonic acid, 2,2,2-trifluoro-1,1-dimethylethyl ester (9CI) (CA INDEX NAME)



RN 737765-56-9 CAPLUS

CN Ethenesulfonic acid, 1-(trifluoromethyl)cyclopentyl ester (9CI) (CA INDEX NAME)



IT 737765-59-2P 737765-60-5P 737765-61-6P

737765-62-7P 737765-63-8P 737765-64-9P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(sulfonates, polymers for resist compns. and patterning process)

RN 737765-59-2 CAPLUS

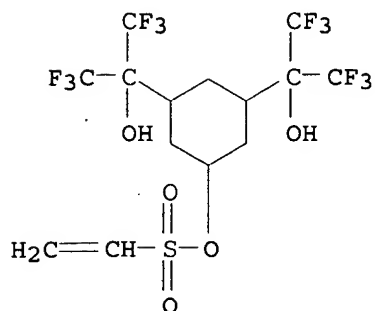
CN Ethenesulfonic acid, 3,5-bis[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl ester, polymer with 2,2,2-trifluoro-1,1-dimethylethyl ethenesulfonate and 5-[3,3,3-trifluoro-2-(methoxymethoxy)-2-

(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-ene (9CI) (CA INDEX NAME)

CM 1

CRN 737765-58-1

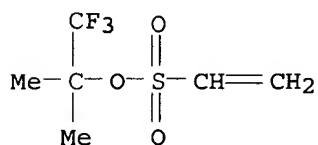
CMF C14 H14 F12 O5 S



CM 2

CRN 737765-55-8

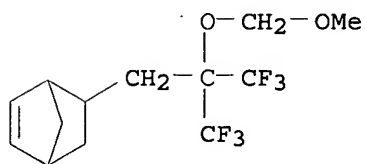
CMF C6 H9 F3 O3 S



CM 3

CRN 450358-92-6

CMF C13 H16 F6 O2



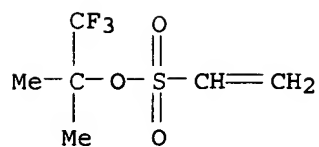
RN 737765-60-5 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol and 2,2,2-trifluoro-1,1-dimethylethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 737765-55-8

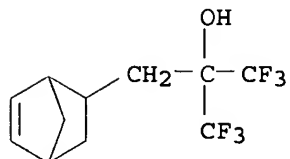
CMF C6 H9 F3 O3 S



CM 2

CRN 196314-61-1

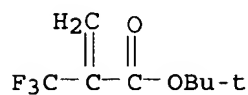
CMF C11 H12 F6 O



CM 3

CRN 105935-24-8

CMF C8 H11 F3 O2



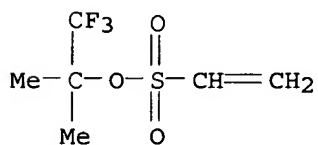
RN 737765-61-6 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with 5-ethenyl- $\alpha,\alpha,\alpha',\alpha'$ -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 2,2,2-trifluoro-1,1-dimethylethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 737765-55-8

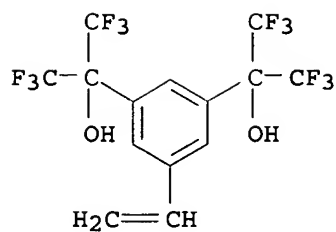
CMF C6 H9 F3 O3 S



CM 2

CRN 568587-26-8

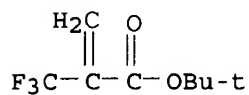
CMF C14 H8 F12 O2



CM 3

CRN 105935-24-8

CMF C8 H11 F3 O2



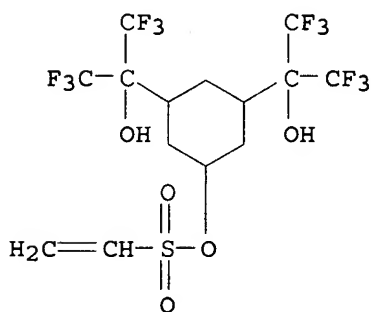
RN 737765-62-7 CAPLUS

CN Ethenesulfonic acid, 3,5-bis[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl ester, polymer with 5-[3,3,3-trifluoro-2-(methoxymethoxy)-2-(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-ene and 1-(trifluoromethyl)cyclopentyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 737765-58-1

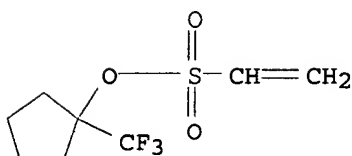
CMF C14 H14 F12 O5 S



CM 2

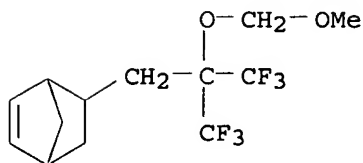
CRN 737765-56-9

CMF C8 H11 F3 O3 S



CM 3

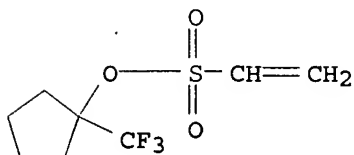
CRN 450358-92-6
CMF C13 H16 F6 O2



RN 737765-63-8 CAPLUS
CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol and 1-(trifluoromethyl)cyclopentyl ethenesulfonate (9CI) (CA INDEX NAME)

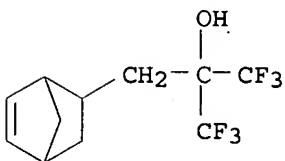
CM 1

CRN 737765-56-9
CMF C8 H11 F3 O3 S



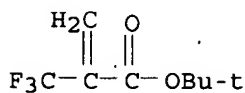
CM 2

CRN 196314-61-1
CMF C11 H12 F6 O



CM 3

CRN 105935-24-8
CMF C8 H11 F3 O2



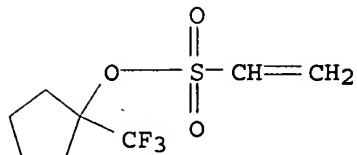
• RN 737765-64-9 CAPLUS
CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with 5-ethenyl- $\alpha,\alpha,\alpha',\alpha'$ -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 1-(trifluoromethyl)cyclopentyl ethenesulfonate

(9CI) (CA INDEX NAME)

CM 1

CRN 737765-56-9

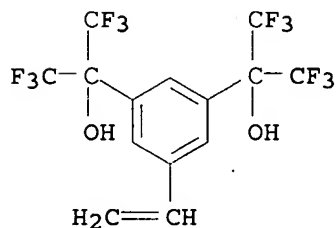
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CM 2

CRN 568587-26-8

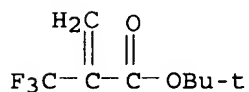
CMF C14 H8 F12 O2



CM 3

CRN 105935-24-8

CMF C8 H11 F3 O2



L3 ANSWER 2 OF 5 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2004:652511 CAPLUS

DN 141:197359

TI Polymers, resist compositions and patterning process

IN Harada, Yuji; Hatakeyama, Jun; Kawai, Yoshio; Sasago, Masaru; Endo, Masayuki; Kishimura, Shinji; Maeda, Kazuhiko; Komoriya, Haruhiko; Miyazawa, Satoru

PA Japan

SO U.S. Pat. Appl. Publ., 27 pp.

CODEN: USXXCO

DT Patent

LA English

FAN.CNT 1

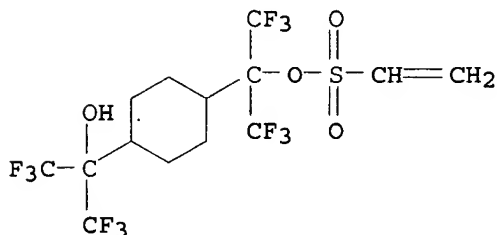
	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2004157155	A1	20040812	US 2004-773228	20040209
	JP 2004244439	A2	20040902	JP 2003-32675	20030210
PRAI	JP 2003-32675	A	20030210		

IT 737763-86-9P 737763-88-1P 737763-89-2P
737763-90-5P

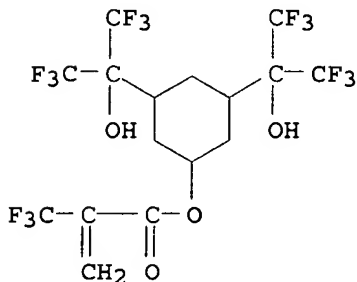
RN 737763-86-9 CAPLUS

CM 1

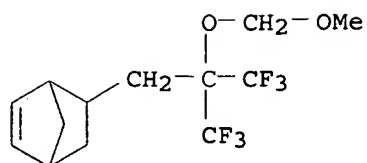
CMF C14 H14 F12 O4 S



CMF C16 H13 F15 O4



CMF C13 H16 F6 O2



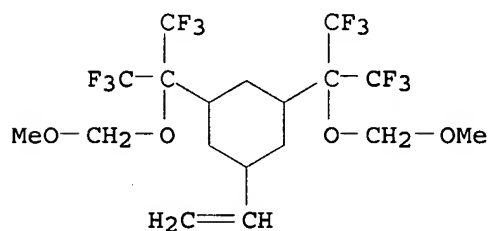
RN 737763-88-1 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 3,5-bis[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl ester, polymer with 1-ethenyl-3,5-bis[2,2,2-trifluoro-1-(methoxymethoxy)-1-(trifluoromethyl)ethyl]cyclohexane and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 737763-87-0

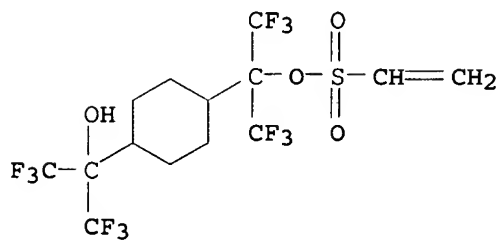
CMF C18 H22 F12 O4



CM 2

CRN 654632-88-9

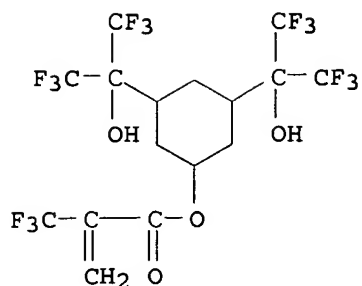
CMF C14 H14 F12 O4 S



CM 3

CRN 585569-92-2

CMF C16 H13 F15 O4



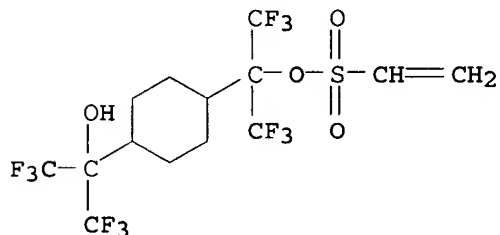
RN 737763-89-2 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 3,5-bis[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl ester, polymer with 1,1-dimethylethyl 2-(trifluoromethyl)-2-propenoate, 5-[3,3,3-trifluoro-2-(methoxymethoxy)-2-(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-ene and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

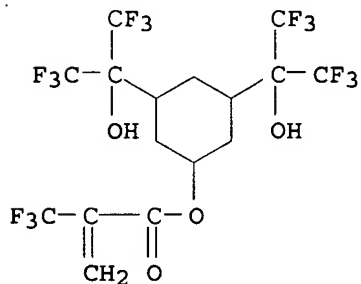
CMF C14 H14 F12 O4 S



CM 2

CRN 585569-92-2

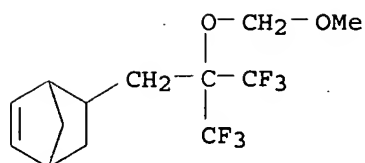
CMF C16 H13 F15 O4



CM 3

CRN 450358-92-6

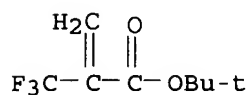
CMF C13 H16 F6 O2



CM 4

CRN 105935-24-8

CMF C8 H11 F3 O2



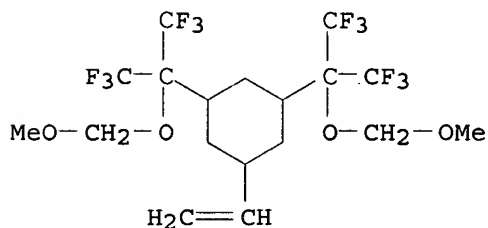
RN 737763-90-5 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 3,5-bis[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl ester, polymer with 1,1-dimethylethyl 2-(trifluoromethyl)-2-propenoate, 1-ethenyl-3,5-bis[2,2,2-trifluoro-1-(methoxymethoxy)-1-(trifluoromethyl)ethyl]cyclohexane and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 737763-87-0

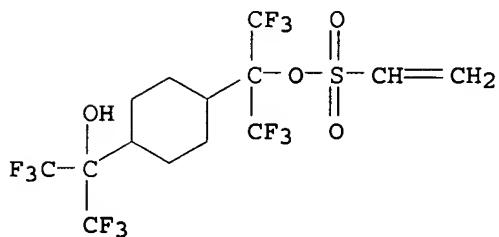
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CM 2

CRN 654632-88-9

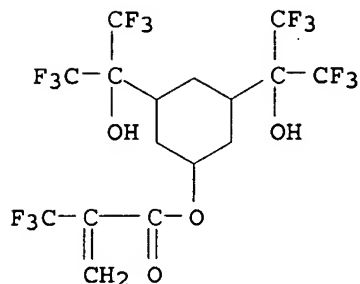
CMF C14 H14 F12 O4 S



CM 3

CRN 585569-92-2

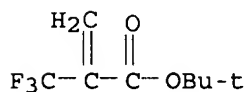
CMF C16 H13 F15 O4



CM 4

CRN 105935-24-8

CMF C8 H11 F3 O2



L3 ANSWER 3 OF 5 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2004:414469 CAPLUS

DN 140:414952

TI Chemical amplification-type resist material containing sulfonate polymer and patterning method

IN Harada, Yuji; Hatakeyama, Jun; Kawai, Yoshio; Sasako, Masaru; Endo, Masataka; Kishimura, Shinji; Maeda, Kazuhiko; Komoritani, Haruhiko; Miyazawa, Satoru

PA Shin-Etsu Chemical Industry Co., Ltd., Japan; Matsushita Electric Industrial Co., Ltd.; Central Glass Co., Ltd.

SO Jpn. Kokai Tokkyo Koho, 40 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2004145048	A2	20040520	JP 2002-310572	20021025
	US 2004144752	A1	20040729	US 2003-690777	20031023
	US 6875556	B2	20050405		
PRAI	JP 2002-310572	A	20021025		

AB The resist material comprises a polymer compound represented by I (r_{1,2} = H, acid unstable group; 0 < a < 1; 0 < b < 1; and 0 < (a + b) ≤ 1) and a polymer compound having a sulfonate repeating unit. The resist material further contains a base compound and a dissoln. inhibitor. The process uses a high energy ray with a wavelength 100-180 nm or 1-30 nm to expose the resist material through a photomask. The resist material exhibited high transparency and alkali dissoln. contrast.

IT 654632-89-0 654632-93-6 688785-36-6

688785-38-8 688785-39-9

RL: POF (Polymer in formulation); TEM (Technical or engineered material use); USES (Uses)

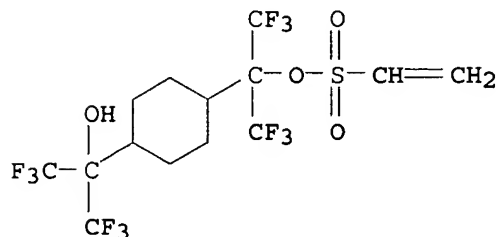
(chemical amplification-type resist material containing sulfonate polymer)

RN 654632-89-0 CAPLUS
 CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer
 with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-
 ethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-
 (trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl
 ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

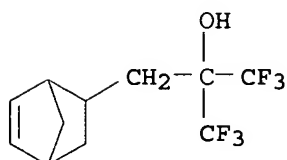
CMF C14 H14 F12 O4 S



CM 2

CRN 196314-61-1

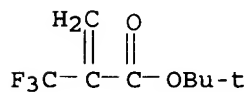
CMF C11 H12 F6 O



CM 3

CRN 105935-24-8

CMF C8 H11 F3 O2

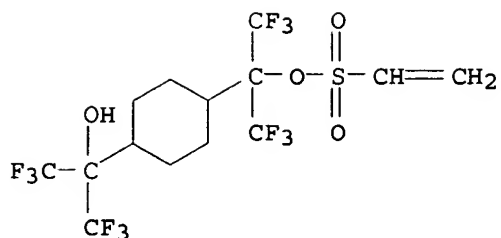


RN 654632-93-6 CAPLUS
 CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer
 with 5-ethenyl- $\alpha,\alpha,\alpha',\alpha'$ -tetrakis(trifluoromethyl)-
 1,3-benzenedimethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-
 1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl
 ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

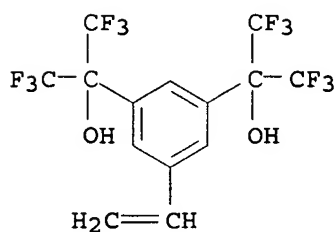
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CM 2

CRN 568587-26-8

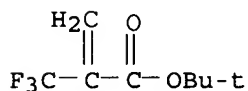
CMF C14 H8 F12 O2



CM 3

CRN 105935-24-8

CMF C8 H11 F3 O2



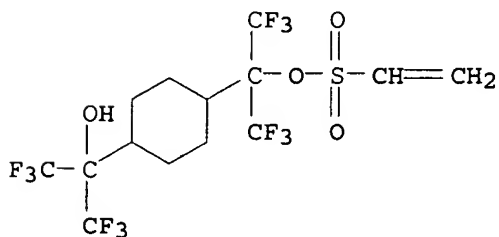
RN 688785-36-6 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with 4-ethenyl- α,α -bis(trifluoromethyl)benzeneethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

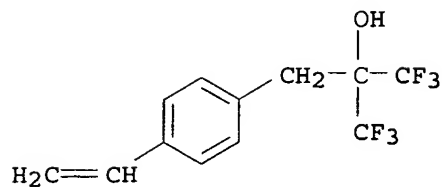
CMF C14 H14 F12 O4 S



CM 2

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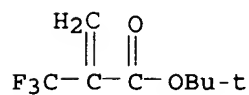
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CM 3

CRN 105935-24-8

CMF C8 H11 F3 O2



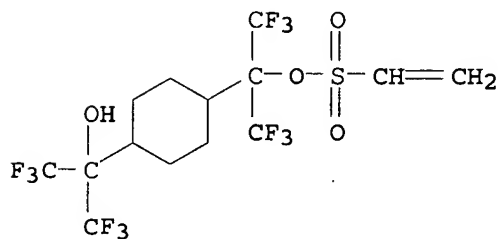
RN 688785-38-8 CAPLUS

CN Ethenesulfonic acid, 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ester, polymer with 1-ethenyl-3,5-bis[2,2,2-trifluoro-1-(methoxymethoxy)-1-(trifluoromethyl)ethyl]benzene and 5-ethenyl- α,α,α' , β -tetrakis(trifluoromethyl)-1,3-benzenedimethanol (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

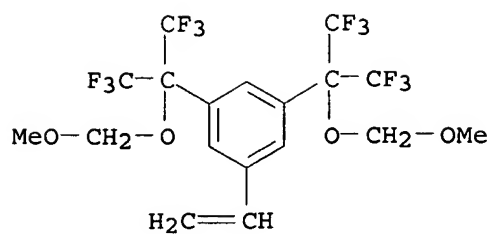
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CM 2

CRN 585573-59-7

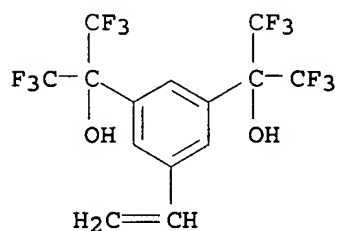
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CM 3

CRN 568587-26-8

CMF C14 H8 F12 O2



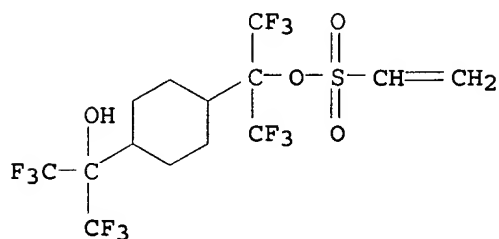
RN 688785-39-9 CAPLUS

CN Carbonic acid, (5-ethenyl-1,3-phenylene)bis[2,2,2-trifluoro-1-(trifluoromethyl)ethylidene] bis(1,1-dimethylethyl) ester, polymer with 5-ethenyl- $\alpha,\alpha,\alpha',\alpha'$ -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

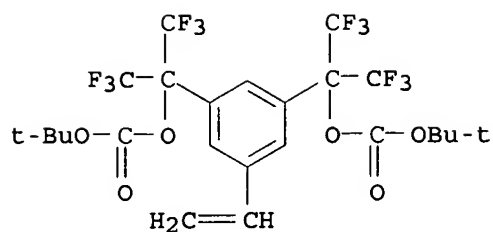
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CM 2

CRN 585573-38-2

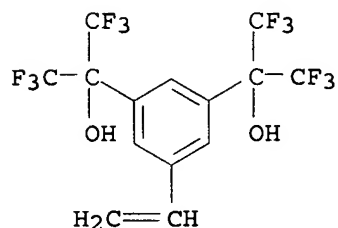
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CM 3

CRN 568587-26-8

CMF C14 H8 F12 O2



L3 ANSWER 4 OF 5 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2004:200317 CAPLUS

DN 140:218236

TI Manufacture of fluoroalkylcyclohexylfluoroalkyl or fluoroalkylphenylfluoroalkyl vinylsulfonates

IN Harada, Yuji; Hatakeyama, Jun; Kawai, Yoshio; Maeda, Kazuhiko; Otani, Michitaka; Komoritani, Haruhiko

PA Shin-Etsu Chemical Industry Co., Ltd., Japan; Central Glass Co., Ltd.

SO Jpn. Kokai Tokkyo Koho, 10 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2004075536	A2	20040311	JP 2002-233377	20020809
PRAI	JP 2002-233377		20020809		

OS MARPAT 140:218236

AB The vinylsulfonates, useful as monomers for chemical amplified vacuum-UV resists, are CH₂:CHSO₃CR₁R₂XCR₃R₄OR₅ [I; R₁, R₂ = H, F, C₁-4 alkyl, fluoroalkyl; R₁ and/or R₂ contain ≥1 F; R₃ and/or R₄ contain ≥1 F; R₅ = H, acid-labile group, C₁-4 oxoalkyl; X = 1,3-cyclohexylene, 1,4-cyclohexylene, 1,3-phenylene, 1,4-phenylene]. Thus, 1,4-di(1,1,1,3,3,3-hexafluoro-2-hydroxypropyl)cyclohexane was treated with ClCH₂CH₂SO₂Cl and pyridine to give 53% I (R₁-R₄ = CF₃, R₅ = H, X = 1,4-cyclohexylene).

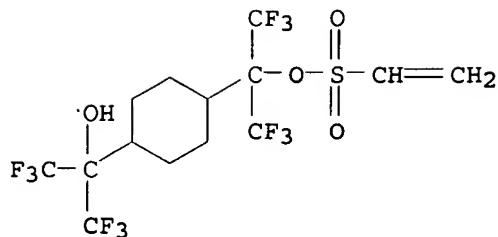
IT 654632-88-9P 654632-95-8P

RL: IMF (Industrial manufacture); PREP (Preparation)

(manufacture of fluoroalkylcyclohexylfluoroalkyl or fluoroalkylphenylfluoroalkyl vinylsulfonates as monomers for chemical amplified vacuum-UV resists)

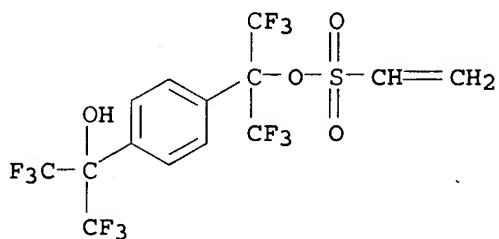
RN 654632-88-9 CAPLUS

CN Ethenesulfonic acid, 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ester (9CI) (CA INDEX NAME)



RN 654632-95-8 CAPLUS

CN Ethenesulfonic acid, 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]phenyl]-1-(trifluoromethyl)ethyl ester (9CI) (CA INDEX NAME)



L3 ANSWER 5 OF 5 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2004:120612 CAPLUS

DN 140:172201

TI Hydrophilic vinylsulfonate derivative polymers, resist compositions and patterning process

IN Harada, Yuji; Hatakeyama, Jun; Kawai, Yoshio; Sasago, Masaru; Endo, Masayuki; Kishimura, Shinji; Maeda, Kazuhiko; Ootani, Michitaka; Komoriya, Haruhiko

PA Shin-Etsu Chemical Co., Ltd., Japan; Matsushita Electric Industrial Co., Ltd.; Central Glass Co., Ltd.

SO U.S. Pat. Appl. Publ., 30 pp.

CODEN: USXXCO

DT Patent

LA English

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2004030079	A1	20040212	US 2003-636692	20030808
	US 6946235	B2	20050920		
	JP 2004067975	A2	20040304	JP 2002-233194	20020809
	US 2005267275	A1	20051201	US 2005-179606	20050713
PRAI	JP 2002-233194	A	20020809		
	US 2003-636692	A3	20030808		

AB A resist composition comprising a polymer containing vinyl sulfonate units having

fluorinated hydrophilic groups based on fluorinated cyclohexane or Ph ring having ether- or OH-containing groups as a base resin has excellent transparency, substrate adhesion and developer penetrability as well as plasma etching resistance, and is suited for lithog. microprocessing. A typical resin was manufactured by radical polymerization of 7 g

2-[4-(2-hydroxy-

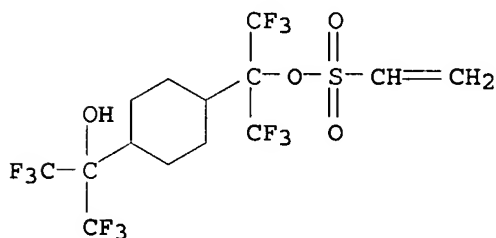
1,1,1,3,3,3-hexafluoro-2-propyl)cyclohexyl]-1,1,1,3,3,3-hexafluoro-2-Pr vinylsulfonate with 7.58 g 6-[2-hydroxy-2-(trifluoromethyl)-3,3,3-trifluoropropyl]norbornene and 5.42 g CH₂=C(CF₃)CO₂CMe₃.

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

RN 654632-89-0 CAPLUS

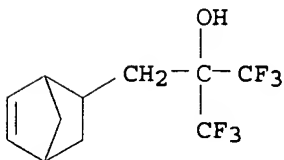
CM 1

CMF C14 H14 F12 O4 S



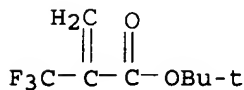
CRN 196314-61-1

CMF C11 H12 F6 O



CRN 105935-24-8

CMF C8 H11 F3 O2



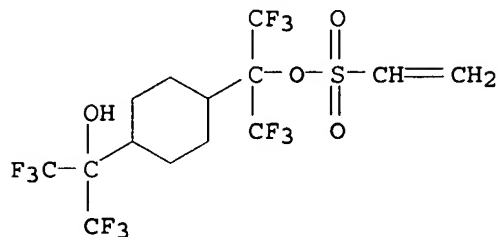
CN 2-Propenoic acid, 2-(trifluoromethyl)-, 2-methyltricyclo[3.3.1.1^{3,7}]dec-2-yl ester, polymer with α,α -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl

ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

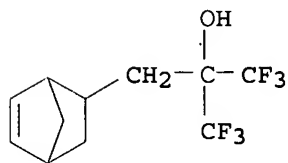
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CM 2

CRN 196314-61-1

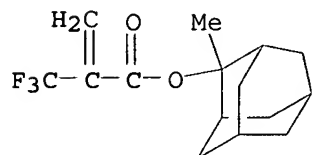
CMF C11 H12 F6 O



CM 3

CRN 188739-86-8

CMF C15 H19 F3 O2



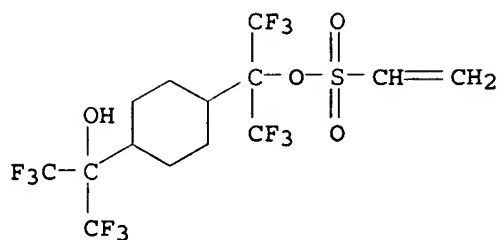
RN 654632-91-4 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with 4-ethenyl- α,α -bis(trifluoromethyl)benzenemethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

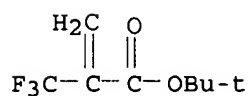
CMF C14 H14 F12 O4 S



CM 2

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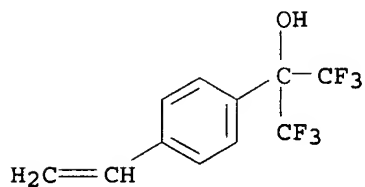
CMF C8 H11 F3 O2



CM 3

CRN 2386-82-5

CMF C11 H8 F6 O



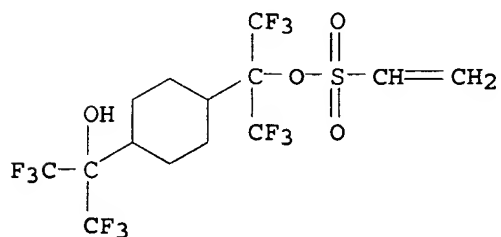
RN 654632-92-5 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 2-methyltricyclo[3.3.1.1^{3,7}]dec-2-yl ester, polymer with 4-ethenyl- α,α -bis(trifluoromethyl)benzenemethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

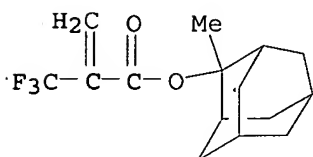
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CM 2

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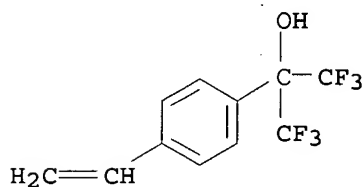
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CM 3

CRN 2386-82-5

CMF C11 H8 F6 O



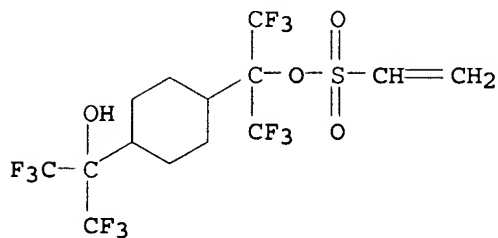
RN 654632-93-6 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with 5-ethenyl- $\alpha,\alpha,\alpha',\alpha'$ -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

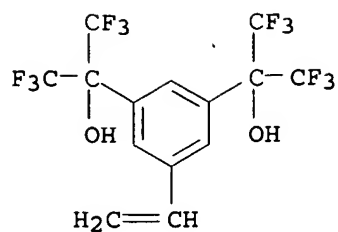
CMF C14 H14 F12 O4 S



CM 2

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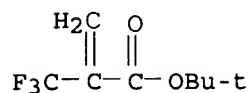
CMF C14 H8 F12 O2



CM 3

CRN 105935-24-8

CMF C8 H11 F3 O2



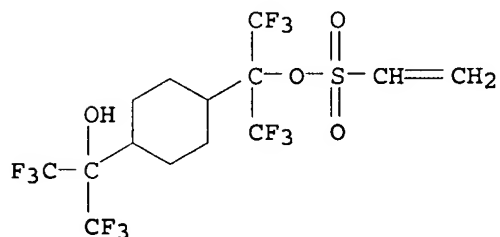
RN 654632-94-7 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 2-methyltricyclo[3.3.1.1^{3,7}]dec-2-yl ester, polymer with 5-ethenyl- $\alpha,\alpha,\alpha',\alpha'$ -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]cyclohexyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-88-9

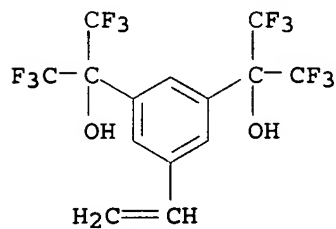
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CM 2

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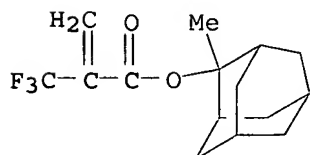
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CM 3

CRN 188739-86-8

CMF C15 H19 F3 O2



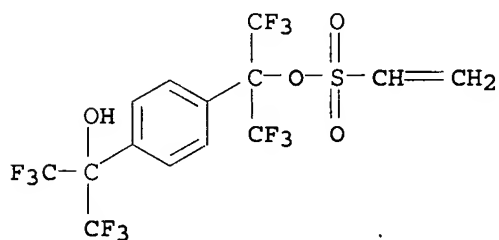
RN 654632-96-9 CAPLUS

CN 2-Propenoic acid, 2-(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with 5-ethenyl- $\alpha,\alpha,\alpha',\alpha'$ -tetrakis(trifluoromethyl)-1,3-benzenedimethanol and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]phenyl]-1-(trifluoromethyl)ethyl ethenesulfonate (9CI) (CA INDEX NAME)

CM 1

CRN 654632-95-8

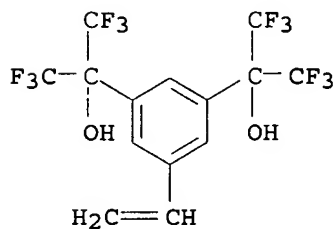
CMF C14 H8 F12 O4 S



CM 2

CRN 568587-26-8

CMF C14 H8 F12 O2



CM 3

CRN 105935-24-8

CMF C8 H11 F3 O2